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(54) **METHOD AND RESULTING CAPACITOR
STRUCTURE FOR LIQUID CRYSTAL ON
SILICON DISPLAY DEVICES**

(75) Inventors: **Herb Huang**, Shanghai (CN); **Wei Min
Li**, Shanghai (CN); **Haiting Li**, Shanghai
(CN); **Ziru Ren**, Shanghai (CN); **Yinan
Han**, Shanghai (CN)

(73) Assignee: **Semiconductor Manufacturing
International (Shanghai) Corporation**,
Shanghai (CN)

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G02F 1/1333 (2006.01)
(52) **U.S. Cl.** **349/38; 349/51; 349/52**
(58) **Field of Classification Search** **349/38; 349/51, 52**
See application file for complete search history.

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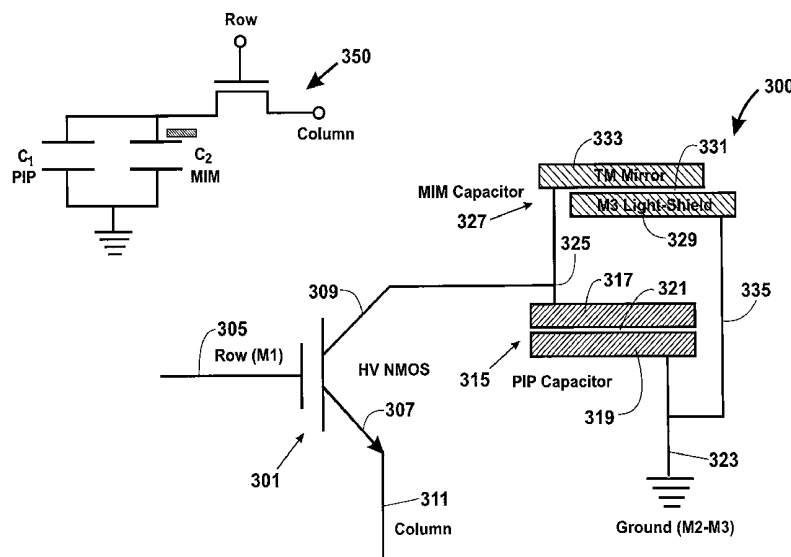
Primary Examiner — Rhonda S Peace

(74) *Attorney, Agent, or Firm* — Kilpatrick Townsend and
Stockton LLP

(57) **ABSTRACT**

In a specific embodiment, the present invention provides an LCOS device. The device has a semiconductor substrate, e.g., silicon substrate. The device has a transistor formed within the semiconductor substrate. The transistor has a first node, a second node, and a row node. A first capacitor structure is coupled to the transistor. The first capacitor structure includes a first polysilicon layer coupled to the second node of the transistor. The first capacitor structure also has a first capacitor insulating layer overlying the first polysilicon layer and a second polysilicon layer overlying the insulating layer. The second polysilicon layer is coupled to a reference potential, e.g., ground. The device has a second capacitor structure coupled to the transistor. The second capacitor structure has a first metal layer coupled to the reference potential, a second capacitor insulating layer, and a second metal layer coupled to the second node of the transistor. A pixel electrode comprises the first metal layer. The pixel electrode is coupled to the second node of the transistor. A mirror surface is on the pixel electrode. The device has a light shielding layer formed from a portion of the second metal layer.

19 Claims, 4 Drawing Sheets



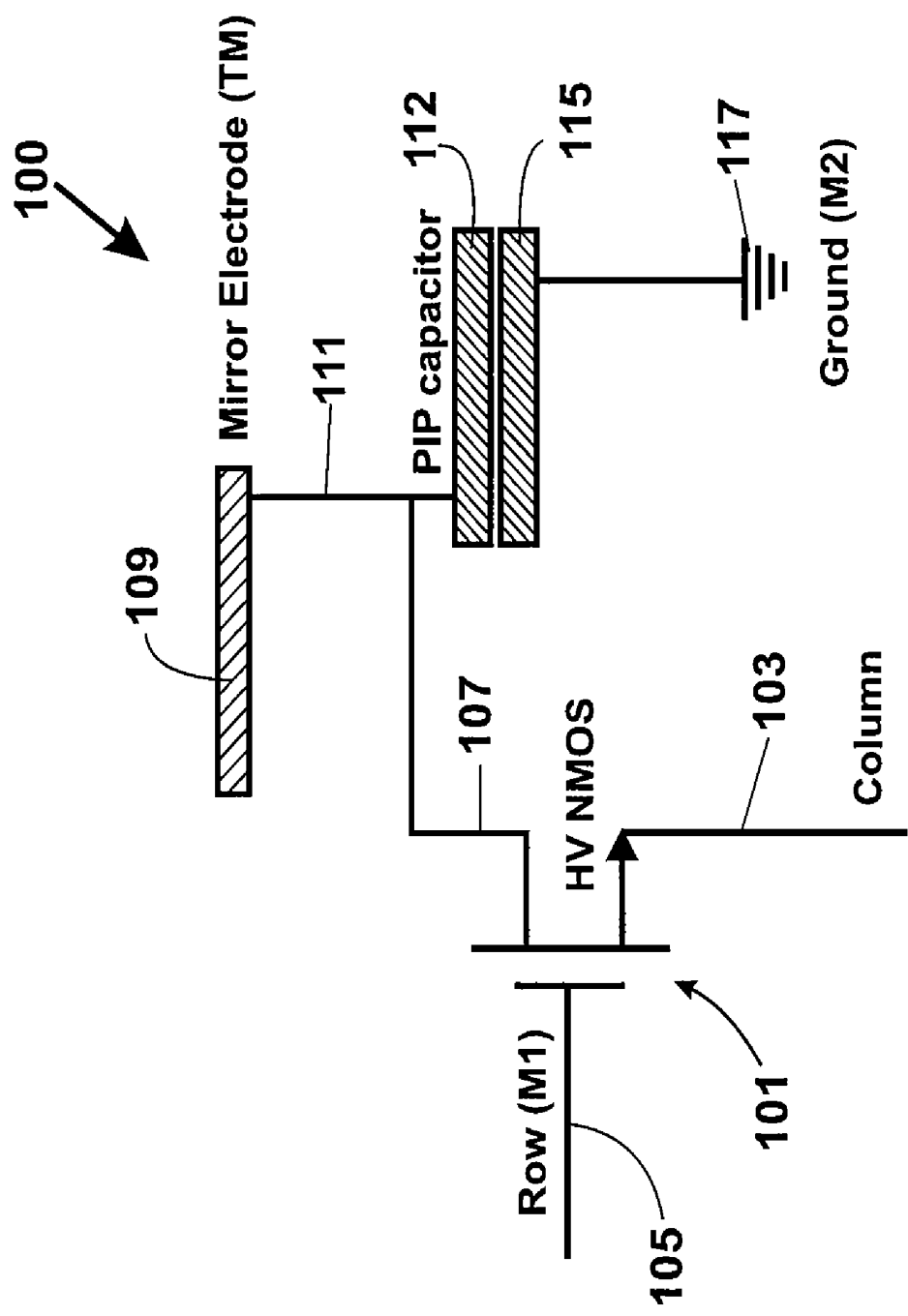


FIGURE 1
(Prior Art)

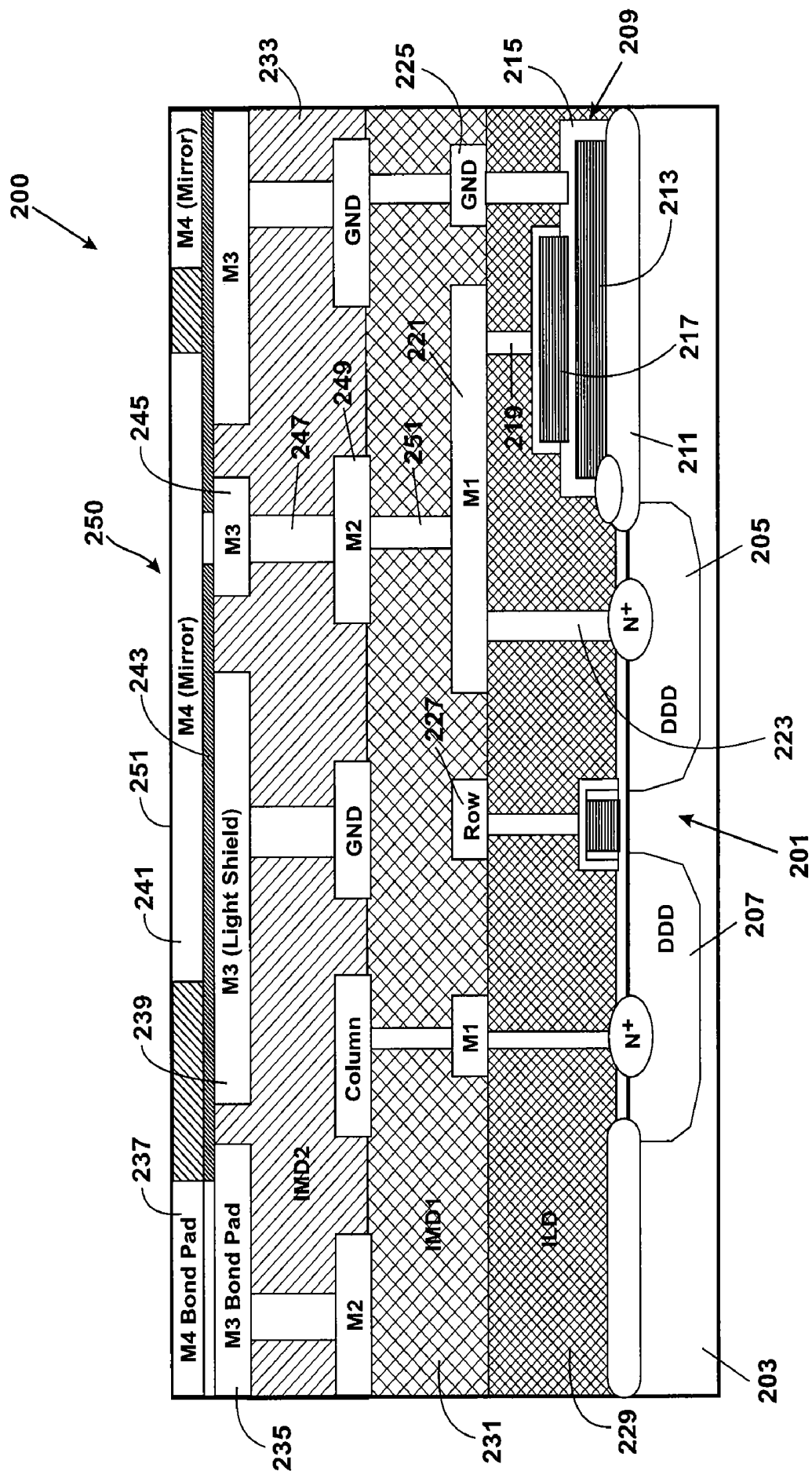


FIGURE 2

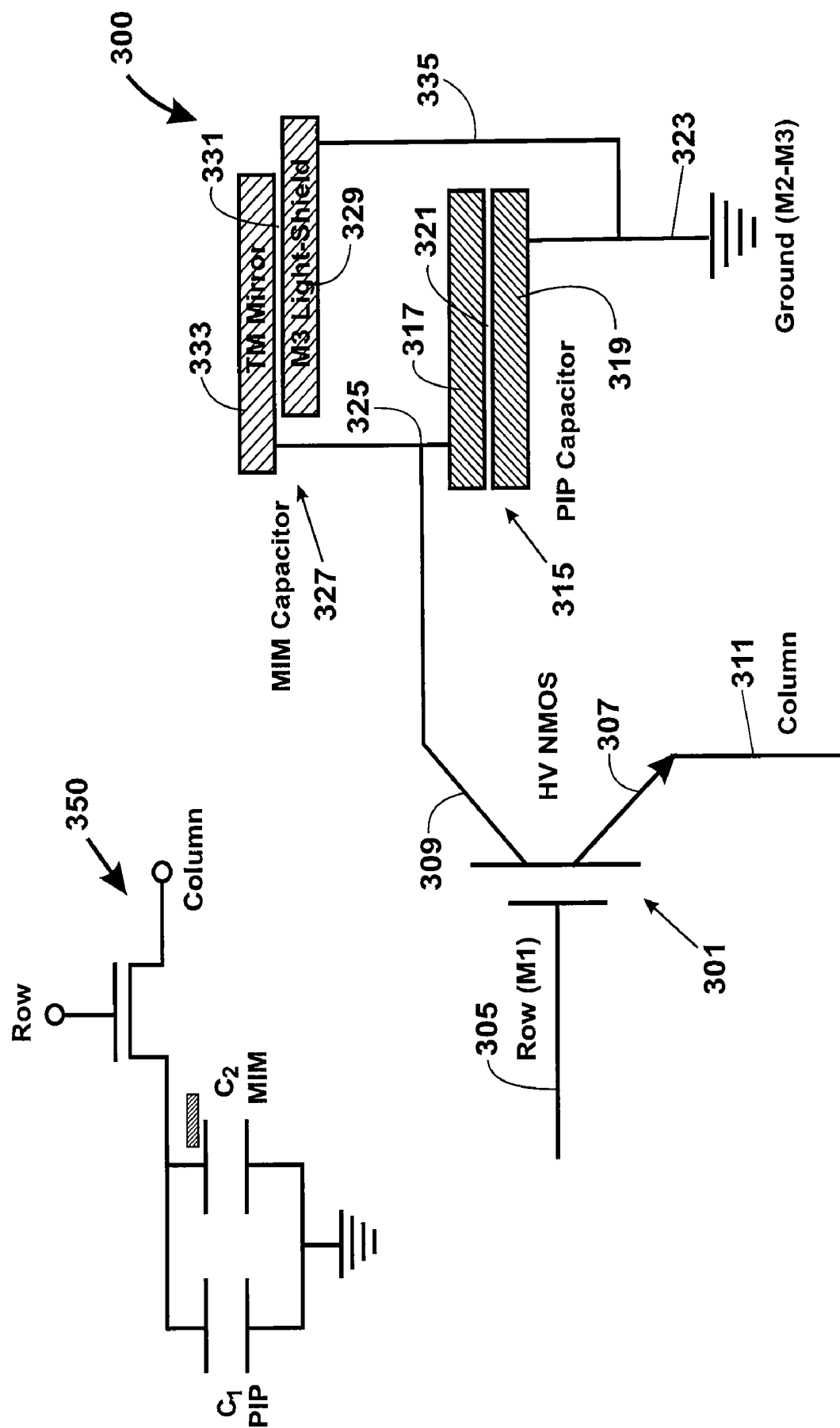


FIGURE 3

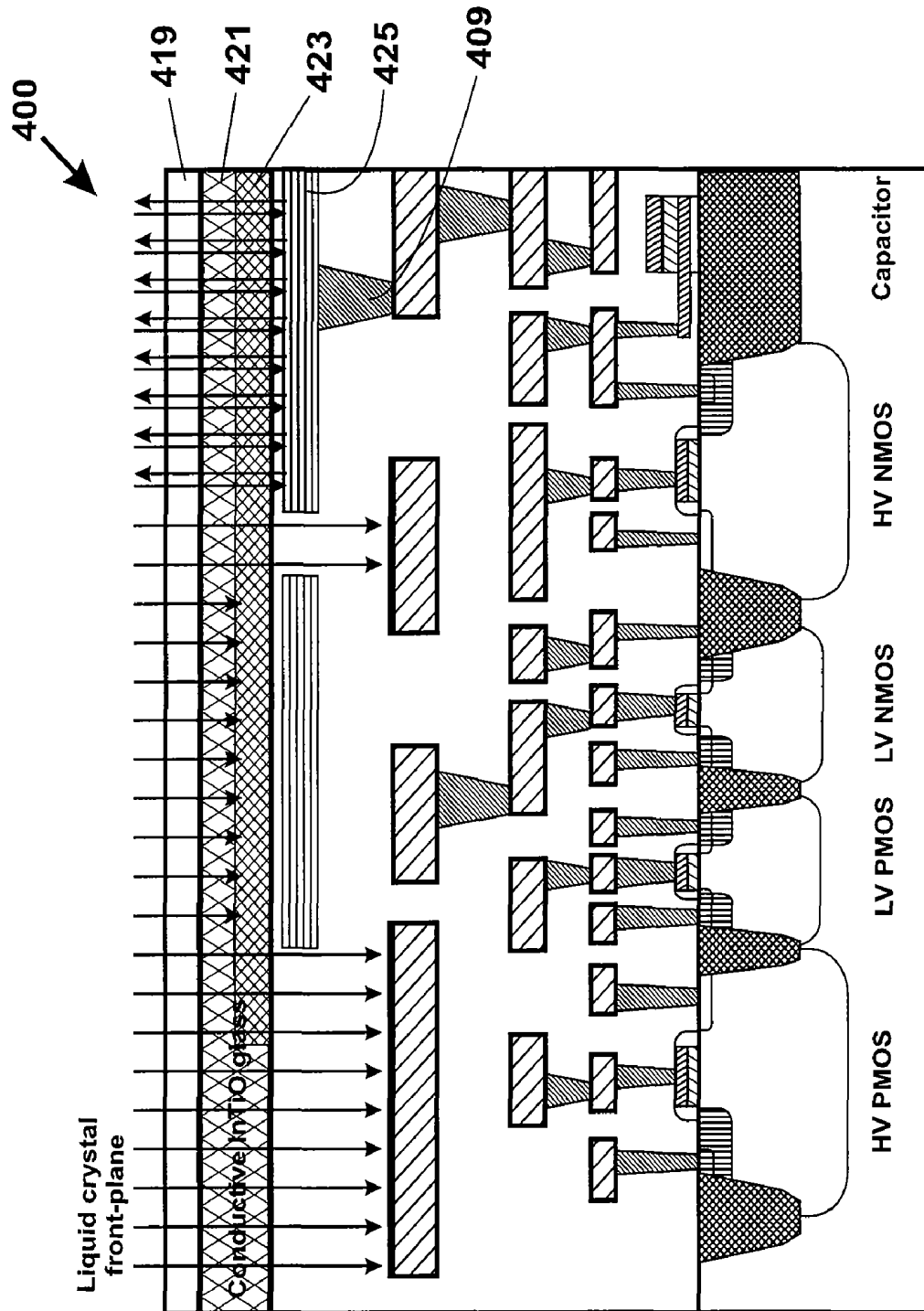


FIGURE 4

METHOD AND RESULTING CAPACITOR STRUCTURE FOR LIQUID CRYSTAL ON SILICON DISPLAY DEVICES

CROSS-REFERENCE TO RELATED APPLICATIONS

This application claims priority to Chinese Application No. 200810040294.5, filed Jul. 3, 2008, commonly assigned, and incorporated herein by reference for all purposes.

BACKGROUND OF THE INVENTION

The present invention is directed to integrated circuits and their processing for the manufacture of electronic devices. More particularly, the invention provides a method for manufacturing a capacitor structure for a liquid crystal on silicon ("LCOS") device for displays. But it would be recognized that the invention has a much broader range of applicability.

Electronic display technologies have rapidly developed over the years. From the early days, cathode ray tube technology, commonly called CRTs, outputted selected pixel elements onto a glass screen in conventional television sets. These television sets originally output black and white moving pictures. Color television sets soon replaced most if not all black and white television units. Although very successful, CRTs were often bulky, difficult to make larger, and had other limitations.

CRTs were soon replaced, at least in part, with liquid crystal panel displays. These liquid crystal panel displays commonly called LCDs used an array of transistor elements coupled to a liquid crystal material and color filter to output moving pictures in color. Many computer terminals and smaller display devices often relied upon LCDs to output video, text, and other visual features. Unfortunately, liquid crystal panels often had low yields and were difficult to scale up to larger sizes. These LCDs were often unsuitable for larger displays often required for television sets and the like.

Accordingly, projection display units have been developed. These projection display units include, among others, a counterpart liquid crystal display, which outputs light from selected pixel elements through a lens to a larger display to create moving pictures, text, and other visual images. Another technology is called "Digital Light Processing" (DLP), which is a commercial name from Texas Instruments Incorporated (TI) of Texas, USA. DLP is often referred to as the use of "micro-mirrors." DLP relies upon a few hundred thousand tiny mirrors, which line up in 800 rows of 600 mirrors each. Each of the mirrors is hinged. An actuator is attached to each of the hinges. The actuator is often electrostatic energy that can tilt each of the mirrors at high frequency. The moving mirrors can modulate light, which can be transmitted through a lens and then displayed on a screen. Although DLP has been successful, it is often difficult to manufacture and subject to low yields, etc.

Yet another technique is called LCOS, which uses both mirrors and liquid crystals. LCOS uses liquid crystals applied to a reflective mirror substrate. As the liquid crystals "open" or "close," light is reflected or blocked, which modulates the light to create an image for display. Often times, there are at least three LCOS chips, each corresponding to light in red, green, and blue channels. LCOS, however, has many limitations. As merely an example, LCOS is often difficult to manufacture. Additionally, LCOS requires at least the three chips that make the projector bulky and heavy and leads to high costs. Accordingly, LCOS has not been adapted to portable projectors.

From the above, it is seen that an improved technique for processing devices is desired.

BRIEF SUMMARY OF THE INVENTION

According to the present invention, techniques for processing integrated circuits for the manufacture of electronic devices are provided. More particularly, the invention provides a method for manufacturing a capacitor structure for a liquid crystal on silicon ("LCOS") device for displays. But it would be recognized that the invention has a much broader range of applicability.

As additional background information, a conventional LCOS backplane CMOS driver usually employs at least the following components in a unit display pixel (See FIG. 1):

1) a high voltage (HV) MOS selector transistor **101**, which includes a row **105**, column **103**, and output **107**;

2) a polysilicon insulator polysilicon (PIP) capacitor, which includes electrodes **115**, **112**, which is coupled to ground **117** and line **111** respectively;

3) an aluminum top metal electrode **109** also as a reflector to incident light; and

4) a subsequent metal light shield to the top metal electrode (TM);

each of these components, taking one or two mask layers of photo/etch processing, operates individually for its assigned but limited functionality. Meanwhile, as the aluminum (Al) top metal becomes even thinner for better reflectivity, it is less feasible to use the top metal for bonding pads. An extra passivation etch is often required to open the bonding pads down to a thicker subsequently lower metal layer for chip bonding. To further increase the performance versus cost ratio, an improvement in the efficiency in comprehensively utilizing the limited layer stack and improving, and even maximizing the performance of an LCOS backplane driver chip is desirable. These and other limitations have been overcome, at least in part and/or whole, by embodiments of the present invention.

In a specific embodiment, the present invention provides an LCOS device. The device has a semiconductor substrate, e.g., silicon substrate. The device has a transistor formed within the semiconductor substrate. The transistor has a first node, a second node, and a row node. A first capacitor structure is coupled to the transistor. The first capacitor structure includes a first polysilicon layer coupled to the second node of the transistor. The first capacitor structure also has a first capacitor insulating layer overlying the first polysilicon layer and a second polysilicon layer overlying the insulating layer. The second polysilicon layer is coupled to a reference potential, e.g., ground. The device has a second capacitor structure coupled to the transistor. The second capacitor structure has a first metal layer coupled to the reference potential, a second capacitor insulating layer, and a second metal layer coupled to the second node of the transistor. A pixel electrode comprises the first metal layer. The pixel electrode is coupled to the second node of the transistor. A mirror surface is on the pixel electrode. The device has a light shielding layer formed from a portion of the second metal layer.

In an alternative specific embodiment, the present invention provides an alternative LCOS device. The device has a semiconductor substrate, e.g., silicon wafer. The device has a high voltage MOS transistor formed within the semiconductor substrate. Preferably, the high voltage MOS transistor has a first source/drain coupled to a first node, a second source/drain coupled to a second node, and a gate coupled to a row node. A PIP capacitor structure is coupled to the HV MOS transistor. Preferably, the PIP capacitor structure has a first polysilicon layer coupled to the second node of the HV MOS transistor, a first capacitor insulating layer overlying the first

polysilicon layer, and a second polysilicon layer overlying the insulating layer. The second polysilicon layer is coupled to a reference potential, e.g., ground potential. A MIM capacitor structure is coupled to the HV MOS transistor. Preferably, the MIM capacitor structure has a first metal layer coupled to the reference potential, a second capacitor insulating layer, and a second metal layer coupled to the second node of the HV MOS transistor. A pixel electrode comprises the first metal layer. Preferably, the pixel electrode is coupled to the second node of the HV MOS transistor. A mirror surface is on the pixel electrode. A light shielding layer is formed from a portion of the second metal layer and a ground potential is coupled to the reference potential. Preferably, the HV MOS device is adapted to switch a voltage potential of about 10 volts to about 20 volts.

In yet an alternative specific embodiment, the invention provides a method for fabricating an LCOS device. The method includes providing a semiconductor substrate. The method also includes forming a transistor structure within the semiconductor substrate. The transistor structure has a first node, a second node, and a row node. The method includes forming a first capacitor structure coupled to the transistor structure. Preferably, the first capacitor structure comprises a first polysilicon layer coupled to the second node of the transistor structure, a first capacitor insulating layer overlying the first polysilicon layer, and a second polysilicon layer overlying the insulating layer. The second polysilicon layer is coupled to a reference potential. The method further includes forming a second capacitor structure coupled to the transistor structure. Preferably, the second capacitor structure comprises a first metal layer coupled to the reference potential, a second capacitor insulating layer, and a second metal layer coupled to the second node of the transistor structure. The method includes forming a pixel electrode comprising the first metal layer. Preferably, the pixel electrode is coupled to the second node of the transistor structure. The method includes forming a mirror surface on the pixel electrode and forming a light shielding layer from a portion of the second metal layer.

Many benefits are achieved by way of the present invention over conventional techniques. For example, the present technique provides an easy to use process that relies upon conventional technology. In some embodiments, the method provides higher device yields in dies per wafer. Additionally, the method provides a process that is compatible with conventional process technology without substantial modifications to conventional equipment and processes. Preferably, the invention provides for an improved capacitor structure for LCOS devices used for displays. Such capacitor structure uses multiple capacitor structures according to preferred embodiments. Certain embodiments of the present invention may include one or more of the following features:

- 1) The unit display pixel has a high voltage (HV) MOS select transistor with its drain electrically connected to an MIM capacitor and a PIP capacitor in parallel;
- 2) The MIM capacitor has a top metal (TM) pixel electrode also as a light reflector and the grounded subsequent metal light-shield, separated by a thin layer of dielectric material such as Si_3N_4 , SiO_2 or Al_2O_3 , or any combination of these and other suitable materials;
- 3) The PIP capacitor has a top polysilicon plate and bottom polysilicon plate, also separated by a thin layer of dielectric material such as Si_3N_4 , SiO_2 or Al_2O_3 or in combination of these and other suitable materials; and
- 4) A thin but wide open via connects the TM and the subsequent metal layer at a bonding pad region to form a stacked, thicker bond pad structure, more robust than a single (ei-

ther TM or subsequent metal) layer bond pad; such a via does not need W plug CVD deposition as it is much thinner than convention IMD dielectric.

Depending upon the embodiment, the present invention in comprehension would expand while integrate feasible functionality of those noted features beyond their conventional settings and thus offer a much-improved value versus cost ratio. In particular, total capacitance built through both the PIP and MIM capacitors in electrically parallel connection on a unit pixel cell could be much increased while more real estate could be relocated to a higher driving current HV MOS transistor. And not only are the TM and the subsequent metal layer utilized for the array pixels' second capacitor, MIM capacitor but also integrated as a more robust bonding pad structure. Depending upon the embodiment, one or more of these benefits may be achieved. These and other benefits will be described in more throughout the present specification and more particularly below.

Various additional objects, features and advantages of the present invention can be more fully appreciated with reference to the detailed description and accompanying drawings that follow.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a simplified diagram of a conventional LCOS pixel cell.

FIG. 2 is a simplified cross-sectional view diagram of an LCOS pixel cell according to an embodiment of the present invention.

FIG. 3 is a simplified circuit diagram of an LCOS pixel cell according to an embodiment of the present invention.

FIG. 4 is a simplified cross-sectional view diagram of an LCOS pixel device according to an embodiment of the present invention.

DETAILED DESCRIPTION OF THE INVENTION

According to the present invention, techniques for processing integrated circuits for the manufacture of electronic devices are provided. More particularly, the invention provides a method for manufacturing a capacitor structure for a liquid crystal on silicon ("LCOS") device for displays. But it would be recognized that the invention has a much broader range of applicability.

FIG. 2 is a simplified cross-sectional view diagram of an LCOS pixel cell according to an embodiment of the present invention. This diagram is merely an example, which should not unduly limit the scope of the claims herein. One of ordinary skill in the art would recognize many variations, alternatives, and modifications. As shown, the present invention provides an LCOS device **200**. The device has a semiconductor substrate **203**, e.g., silicon wafer. The device has a high voltage MOS transistor **201** formed within the semiconductor substrate. Preferably, the high voltage MOS transistor has a first source/drain **207** coupled to a first node, a second source/drain **205** coupled to a second node, and a gate coupled to a row node **227**. The source/drain regions include a double diffused drain region (DDD) and N+ type plug implant region. Preferably, the first node is coupled to metal 1 via plug, which is coupled to a column node. The device also includes interlayer dielectric layer **229**, e.g., borophosphosilicate glass (BPSG), phosphosilicate glass (PSG), fluorinated silicate glass (FSG). The device also includes inter metal layer dielectric (IMD1) **231**, which is overlying the metal 1 layer.

A PIP capacitor structure **209** is coupled to the HV MOS transistor. Preferably, the PIP capacitor structure has a first

polysilicon layer **217** coupled to the second node **223** of the HV MOS transistor, a first capacitor insulating layer **215** overlying the first polysilicon layer, and a second polysilicon layer **213** overlying the insulating layer. The second polysilicon layer is coupled to a reference potential **225**, e.g., ground potential. The second polysilicon layer is also overlying isolation region **211**, which can be field isolation oxide or other suitable isolation structure. As also shown, the first polysilicon layer is connected to plug layer **219**, which is coupled to metal 1 layer **221**, which couples to plug layer **223**, which couples to source/drain region **205**. The PIP capacitor insulating layer comprises a silicon dioxide material having a thickness ranging from about 500 Angstroms to about 1500 Angstroms. The insulating layer is made of a material selected from Si_3N_4 , SiO_2 , or Al_2O_3 , or any combination of these, and other suitable materials.

A MIM capacitor structure **250** is coupled to the HV MOS transistor. Preferably, the MIM capacitor structure has a first metal layer **239** coupled to the reference potential, a second capacitor insulating layer **243**, and a second metal layer **241** coupled to the second node of the HV MOS transistor. The second metal layer is coupled to metal 3 **245**, which is coupled to plug layer **247**, which is coupled to metal 2 **249**, which is coupled to plug layer **251**, which is coupled to metal 1 **221**, which is coupled to plug layer **223**, which is coupled to source/drain region **205** of the HV NMOS device. The capacitor insulating layer is made of a material selected from Si_3N_4 , SiO_2 , or Al_2O_3 , or any combination of these, and other suitable materials.

A pixel electrode comprises the first metal layer. Preferably, the pixel electrode is coupled to the second node of the HV MOS transistor. A mirror surface **251** is on the pixel electrode. A light shielding layer **239** is formed from a portion of the second metal layer and a ground potential is coupled to the reference potential. Preferably, the HV MOS device is adapted to switch a voltage potential of about 10 volts to about 20 volts.

The device also includes bonding pad made of metal 4 **237**, which is overlying a portion **235** of metal 3, which is also a portion of the bonding pad. The bonding pad is coupled to a plug, which is coupled to the metal 2 layer. Of course, there can be other variations, modifications, and alternatives.

Depending upon the embodiment, there can be many variations to the above embodiment. As merely an example, the first metal layer for the MIM capacitor comprises an aluminum bearing material. The second metal layer for the MIM capacitor also comprises an aluminum bearing material. In a specific embodiment, the first metal layer has an area of about 30 square micrometers to about 100 square micrometers. For the PIP capacitor, the first polysilicon layer comprises a doped polysilicon material and the second polysilicon layer comprises a doped polysilicon material. Additionally, the PIP capacitor has a capacitance value ranging from about 50 to 100 Femto Farads according to a specific embodiment. The MIM capacitor has a capacitance value ranging from about 5 to 100 Femto Farads according to a specific embodiment.

Of course, one of ordinary skill in the art would recognize other variations, modifications, and alternatives. Further details of the present LCOS device can be found throughout the present specification and more particularly below. FIG. **3** is a simplified circuit diagram of an LCOS pixel cell according to an embodiment of the present invention. This diagram is merely an example, which should not unduly limit the scope of the claims herein. One of ordinary skill in the art would recognize many variations, alternatives, and modifications. As shown, the present invention provides an LCOS device. The device has a semiconductor substrate, e.g., silicon

wafer. The device has a high voltage MOS transistor **301** formed within the semiconductor substrate. Preferably, the high voltage MOS transistor has a first source/drain **307** coupled to a first node **311**, a second source/drain **309** coupled to a second node **325**, and a gate coupled to a row node **305**.

A PIP capacitor structure **315** is coupled to the HV MOS transistor. Preferably, the PIP capacitor structure has a first polysilicon layer **317** coupled to the second node of the HV MOS transistor, the first polysilicon layer overlies a first capacitor insulating layer **321**, and the first capacitor insulating layer overlies a second polysilicon layer **319**. The second polysilicon layer is coupled to a reference potential **323**, e.g., ground potential.

A MIM capacitor structure **327** is coupled to the HV MOS transistor. Preferably, the MIM capacitor structure has a first metal layer **329** coupled to the reference potential **335**, a second capacitor insulating layer **331**, and a second metal layer **333** coupled to the second node **325** of the HV MOS transistor. Preferably, the PIP capacitor structure and the MIM capacitor structure are adapted to hold a charge value associated with maintaining a predetermined voltage potential on the pixel electrode.

A pixel electrode comprises the first metal layer. Preferably, the pixel electrode is coupled to the second node of the HV MOS transistor. A mirror surface is on the pixel electrode. A light shielding layer **329** is formed from a portion of the second metal layer and a ground potential is coupled to the reference potential. Preferably, the HV MOS device is adapted to switch a voltage potential of about 10 volts to about 20 volts. A circuit representation **350** is also illustrated. As shown, the PIP and MIM capacitor structures are connected in parallel to each other according to a specific embodiment.

FIG. **4** is a simplified cross-sectional view diagram of an LCOS pixel device **400** according to an embodiment of the present invention. This diagram is merely an example, which should not unduly limit the scope of the claims herein. One of ordinary skill in the art would recognize many variations, alternatives, and modifications. As shown, the LCOS device has a semiconductor substrate, e.g., silicon wafer. An MOS device layer is formed overlying the semiconductor substrate. Preferably, the MOS device layer has a plurality of MOS devices. Each of the MOS devices has a contact region for an electrode and a contact region for a voltage potential. A planarized interlayer dielectric layer is formed overlying the MOS device layer. The LCOS device also has a plurality of recessed regions (e.g., damascene structures) within a portion of the interlayer dielectric layer and a metal layer (e.g., aluminum) to fill each of the recessed regions to form respective plurality of electrode regions **425** corresponding to each of the recessed regions. Preferably, the metal layer has been plated into each of the damascene structures. Each of the electrode regions is respectively coupled to at least one of the MOS devices among the plurality of MOS devices via interconnect structure **409**, which may be a plug or other like structure. A protective layer is formed overlying surface regions of each of the plurality of electrode regions to protect the surface regions. A mirror finish is on each of the surface regions. Preferably, the mirror finish is substantially free from dishes and scratches from a chemical mechanical polishing process. Each of the electrodes may have a thickness ranging from about 2000 Angstroms to about 4000 Angstroms and can be at other dimensions. Each of the electrodes represents a pixel element in an array of pixel elements for the LCOS device. Also shown are liquid crystal film **423** overlying the electrodes. The LCOS device also has a transparent electrode layer **421** (e.g., indium tin oxide) and an overlying glass plate **419** to enclose the multilayered structure. Details on ways of

operating the LCOS device can be found throughout the present specification and more particularly below.

To operate the LCOS device, light traverses through the glass cover, through the transparent electrode, and to the liquid crystal film. When the electrode is not biased, the liquid crystal film is essentially in the off position, which does not allow the light to pass therethrough. Rather, light is blocked and does not reflect off of the mirror surface of the electrode. When the electrode is biased via MOS device, the liquid crystal film is in an on-position, which allows light to pass. The light reflects off of the surface of the electrode and through the liquid crystal film, which is in an on-position. Preferably, the mirror surface is substantially free from imperfections. Accordingly, at least 93% of the incoming light passes out of the LCOS device. Details on ways of fabricating the LCOS device can be found throughout the present specification and more particularly below.

A method for fabricating an electrode structure for an LCOS device according to an embodiment of the present invention may be outlined as follows:

1. Provide a semiconductor substrate;
2. Form a transistor structure within the semiconductor substrate, where the transistor structure has a first node, a second node, and a row node;
3. Form a first capacitor structure coupled to the transistor structure, where the first capacitor structure comprises a first polysilicon layer coupled to the second node of the transistor structure, a first capacitor insulating layer overlying the first polysilicon layer, and a second polysilicon layer overlying the insulating layer;
4. Form a second capacitor structure coupled to the transistor structure, where the second capacitor structure comprises a first metal layer coupled to the reference potential, a second capacitor insulating layer, and a second metal layer coupled to the second node of the transistor structure;
5. Form a pixel electrode comprising the first metal layer;
6. Form a mirror surface on the pixel electrode;
7. Form a light shielding layer from a portion of the second metal layer;
8. Provide a liquid crystal layer overlying the pixel electrode, a transparent electrode layer overlying the liquid crystal layer, and a glass layer overlying the transparent electrode layer to form the LCOS device; and
9. Perform other steps, as desired.

The above sequence of steps provides a method according to an embodiment of the present invention. As shown, the method uses a combination of steps including a way of forming a plurality of capacitor structures for an LCOS device. Other alternatives can also be provided where steps are added, one or more steps are removed, or one or more steps are provided in a different sequence without departing from the scope of the claims herein.

It is also understood that the examples and embodiments described herein are for illustrative purposes only and that various modifications or changes in light thereof will be suggested to persons skilled in the art and are to be included within the spirit and purview of this application and scope of the appended claims.

What is claimed is:

1. An LCOS device comprising:
 - a semiconductor substrate;
 - a transistor formed within the semiconductor substrate, the transistor having a first node, a second node, and a row node;
 - a first capacitor structure coupled to the transistor, the first capacitor structure comprising:

- a first polysilicon layer coupled to the second node of the transistor;
- a first capacitor insulating layer overlying the first polysilicon layer;
- a second polysilicon layer overlying the insulating layer, the second polysilicon layer being coupled to a reference potential;
- a second capacitor structure coupled to the transistor, the second capacitor structure comprising:
 - a first metal layer coupled to the reference potential;
 - a second capacitor insulating layer;
 - a second metal layer coupled to the second node of the transistor;
- a pixel electrode comprising the first metal layer, the pixel electrode being coupled to the second node of the transistor;
- a mirror surface on the pixel electrode; and
- a light shielding layer formed from a portion of the second metal layer.

2. The device of claim 1 wherein the reference potential is ground.

3. The device of claim 1 wherein the first metal layer comprises an aluminum bearing material.

4. The device of claim 1 wherein the second metal layer comprises an aluminum bearing material.

5. The device of claim 1 wherein the first polysilicon layer comprises a doped polysilicon material.

6. The device of claim 1 wherein the second polysilicon layer comprises a doped polysilicon material.

7. The device of claim 1 wherein the first metal layer has an area of about 30 square micrometers to about 100 square micrometers.

8. The device of claim 1 wherein the second capacitor is a PIP capacitor having a capacitance value ranging from about 50 to 100 Fempto Farads.

9. The device of claim 1 wherein the first capacitor is a MIM capacitor having a capacitance value ranging from about 5 to 100 Fempto Farads.

10. The device of claim 1 wherein the second capacitor insulating layer comprises a silicon dioxide material having a thickness ranging from about 500 Angstroms to about 1500 Angstroms.

11. The device of claim 1 wherein the transistor is a high voltage NMOS device adapted to switch a voltage of about 10 volts to about 20 volts.

12. The device of claim 1 wherein the first capacitor and the second capacitor are connected to each other in parallel.

13. The device of claim 1 wherein the second capacitor insulating layer is made of a material selected from Si_3N_4 , SiO_2 , or Al_2O_3 .

14. The device of claim 1 wherein the first capacitor insulating layer is made of a material selected from Si_3N_4 , SiO_2 , or Al_2O_3 .

15. An LCOS device comprising:

- a semiconductor substrate;
- a high voltage MOS transistor formed within the semiconductor substrate, the high voltage MOS transistor having a first source/drain coupled to a first node, a second source/drain coupled to a second node, and a gate coupled to a row node;
- a PIP capacitor structure coupled to the HV MOS transistor, the PIP capacitor structure comprising:
 - a first polysilicon layer coupled to the second node of the HV MOS transistor;
 - a first capacitor insulating layer overlying the first polysilicon layer;

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a second polysilicon layer overlying the insulating layer, the second polysilicon layer being coupled to a reference potential;

a MIM capacitor structure coupled to the HV MOS transistor, the MIM capacitor structure comprising:

a first metal layer coupled to the reference potential;

a second capacitor insulating layer;

a second metal layer coupled to the second node of the HV MOS transistor;

a pixel electrode comprising the first metal layer, the pixel electrode being coupled to the second node of the HV MOS transistor;

a mirror surface on the pixel electrode;

a light shielding layer formed from a portion of the second metal layer;

a ground potential coupled to the reference potential.

16. The device of claim **15** wherein the HV MOS device is adapted to switch a voltage potential of about 10 volts to about 20 volts.

17. The device of claim **15** wherein the PIP capacitor is connected to the MIM capacitor in parallel configuration.

18. The device of claim **15** wherein the PIP capacitor structure and the MIM capacitor structure are adapted to hold a charge value associated with maintaining a predetermined voltage potential on the pixel electrode.

19. A method for fabricating an LCOS device, the method comprising:

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providing a semiconductor substrate;

forming a transistor structure within the semiconductor substrate, the transistor structure having a first node, a second node, and a row node;

forming a first capacitor structure coupled to the transistor structure, the first capacitor structure comprising:

a first polysilicon layer coupled to the second node of the transistor structure;

a first capacitor insulating layer overlying the first polysilicon layer;

a second polysilicon layer overlying the insulating layer, the second polysilicon layer being coupled to a reference potential;

forming a second capacitor structure coupled to the transistor structure, the second capacitor structure comprising:

a first metal layer coupled to the reference potential;

a second capacitor insulating layer;

a second metal layer coupled to the second node of the transistor structure;

forming a pixel electrode comprising the first metal layer, the pixel electrode being coupled to the second node of the transistor structure;

forming a mirror surface on the pixel electrode; and

forming a light shielding layer from a portion of the second metal layer.

* * * * *

专利名称(译)	用于硅显示器件上的液晶的方法和所得到的电容器结构		
公开(公告)号	US7936406	公开(公告)日	2011-05-03
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[标]申请(专利权)人(译)	SEICONDUCTOR MFG INT上海CORP		
申请(专利权)人(译)	SEICONDUCTOR中芯国际 (上海) 有限公司		
当前申请(专利权)人(译)	中芯国际集成电路制造 (上海) 有限公司		
[标]发明人	HUANG HERB LI WEI MIN LI HAITING REN ZIRU HAN YINAN		
发明人	HUANG, HERB LI, WEI MIN LI, HAITING REN, ZIRU HAN, YINAN		
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摘要(译)

在特定实施例中，本发明提供LCOS设备。该器件具有半导体衬底，例如硅衬底。该器件具有在半导体衬底内形成的晶体管。晶体管具有第一节点，第二节点和行节点。第一电容器结构耦合到晶体管。第一电容器结构包括耦合到晶体管的第二节点的第一多晶硅层。第一电容器结构还具有覆盖第一多晶硅层的第一电容器绝缘层和覆盖绝缘层的第二多晶硅层。第二多晶硅层耦合到参考电位，例如地。该器件具有耦合到晶体管的第二电容器结构。第二电容器结构具有耦合到参考电位的第一金属层，第二电容器绝缘层，以及耦合到晶体管的第二节点的第二金属层。像素电极包括第一金属层。像素电极耦合到晶体管的第二节点。镜面位于像素电极上。该器件具有由第二金属层的一部分形成的光屏蔽层。

